

# ***Published results presented in printed form***

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## ***Dental / Medical***

### **Dental MRI**

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### **TMD therapy and diagnostics**

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## Oral Presentations

K Rottner et al. **Deutsche Gesellschaft für Grundlagenforschung**, Mainz 2008

K. Rottner et al, **Deutsche Gesellschaft für Zahnärztliche Prothetik und Werkstoffkunde**, Düsseldorf (2008)

K. Rottner et al, **Deutsche Gesellschaft für Zahnärztliche Prothetik und Werkstoffkunde**, Bonn (2007)

K. Rottner et al, **Gemeinschaftstagung der Schweizerischen und deutschen Gesellschaft für Zahnärztl. Prothetik und Werkstoffkunde**, Basel, Switzerland (2006)

K Rottner et al., **International Congress of the World Association of Sleep Medicine**, Berlin, Germany (2005)

K Rottner et al., (Invited talk, opening address of the “Device Development” session) at the **European Conference on SiC**, Montpellier, France (1998)

K. Rottner et al, **International Conference on SiC**, Stockholm, Sweden (1997)

K. Rottner et al. **European Conference on SiC**, Crete, Greece (1996)

K. Rottner et al. **Material Research Society Spring Meeting**, San Francisco, USA (1996)

K Rottner, et al **International Conference on SiC**, Kyoto, Japan, (1995)

K Rottner, et al. **Material Research Society Spring Meeting**, San Francisco, USA (1994)

K Rottner et al. **DPG Spring Meeting**, Regensburg (1992)

... plus a series of poster presentations on international meetings.